

ABSTRACT

Disclosed is a bit line-manufacturing method, by which a bit line having a fine width can be easily manufactured. The method comprises the steps of: successively forming a
5 conducting layer and an insulating layer on a substrate, the conducting layer serving to form a bit line; forming a first mask pattern on the insulating layer in such a manner that a desired region of the insulating layer is exposed; etching the first mask pattern, so as to form a second mask pattern;
10 removing the insulating layer using the second mask pattern; removing the second mask pattern; and removing the conducting layer using the remaining insulating layer as a mask, so as to form the bit line.

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